

b) Amendment to the Claims

Please cancel claims 1-4 without prejudice or disclaimer of the subject matter therein. Please add new claims 13-25 as follows. The status of all the claims is listed below.

Claims 1. - 11. (Cancelled)

12. (Previously Presented) A plasma treatment apparatus comprising:
a plurality of reactors each having an evacuable inside where at least one treatment substrate is set in, and having impedances different from each other;
a high-frequency power supply means for supplying high-frequency power into each reactor having been inside-evacuated, to cause glow discharge to take place in the reactor, wherein each of the reactors and the high-frequency power supply means are provided separately;
a plurality of impedance regulation means provided correspondingly to the impedances of each of the reactors in order to regulate impedances on the side of each reactor and on the side of the high-frequency power supply means; and
a moving means for moving the reactors.

13. (New) The plasma treatment apparatus of claim 12, wherein the substrate is a substrate for an electrophotographic photosensitive member.

14. (New) A plasma treatment method comprising:

- (a) successively connecting a plurality of movable reactors, each reactor provided with a cylindrical substrate evacuated inside of the reactor, to a high-frequency power supply;
- (b) supplying high-frequency power into the reactors via impedance regulation means provided in each of the reactors;
- (c) generating a glow discharge from the supplied high-frequency power to treat a surface of the cylindrical substrate; and
- (d) successively separating the plurality of reactors after the surface treatment from the high-frequency power supply.

15. (New) The plasma treatment method according to claim 14, wherein the surface of the substrate is plasma treated by deposited film formation.

16. (New) The plasma treatment method according to claim 15, wherein the deposited film is a deposited film of an electrophotographic photosensitive member.

17. (New) The plasma treatment method according to claim 14, wherein a plurality of the cylindrical substrates having a predetermined diameter are provided in one of the reactors, and a plurality of the cylindrical substrates having a

diameter different from the predetermined diameter are provided in another one of the reactors.

18. (New) A plasma treatment method comprising:

- (a) successively connecting a plurality reactors, each provided with (i) a cylindrical substrate evacuated inside of the reactor and (ii) a different impedance, to a high-frequency power supply;
- (b) supplying high-frequency power to the reactors via impedance regulation means corresponding to the reactors and mounted at a detachable attachment portion provided at the high-frequency power supply;
- (c) generating a glow discharge from the supplied high-frequency power to treat a surface of the cylindrical substrate; and
- (d) successively separating the plurality of reactors after the surface treatment from the high-frequency power supply.

19. (New) The plasma treatment method according to claim 18, wherein the surface of the substrate is plasma treated by deposited film formation.

20. (New) The plasma treatment method according to claim 19, wherein the deposited film is a deposited film of an electrophotographic photosensitive member.

21. (New) The plasma treatment method according to claim 18, wherein a plurality of the cylindrical substrates having a predetermined diameter are provided in one of the reactors, and a plurality of the cylindrical substrates having a diameter different from the predetermined diameter are provided in another one of the reactors.

22. (New) The plasma-treatment method according to claim 14, wherein the impedance is regulated by electrostatic capacitance.

23. (New) The plasma-treatment method according to claim 14, wherein the impedance is regulated by inductance coefficient.

24. (New) The plasma-treatment method according to claim 18, wherein the impedance is regulated by electrostatic capacitance.

25. (New) The plasma-treatment method according to claim 18, wherein the impedance is regulated by inductance coefficient.